



Référence Part number BP 1313 A01

mm
(inch)

Boîtier de puissance BP 1313 TO 254 Power Package

Description

In glass to metal seal this package characterized by a high thermal conductivity and high current is specially designed for hermetic encapsulation of power transistors, and thyristors.

Characteristics

- **Steel frame** and alloy (copper base, hard brazing assembly).
- **Pins:** nickel-iron with copper core.
- **Finishing:** — electroless nickel plating
— full or selective gold plating on pins over nickel underplating...
- **Maximum operating temperature:** 400°C
- **Dielectric withstanding voltage:** 700 V peak
- **Maximum direct current:** 20 A
- **Insulation resistance:** 10⁴ MΩ
- **Typical junction-base thermal resistance (°C/W):**

| chip sizes (mm ²) | 25 | 50 | 100 |
|-------------------------------|------|------|------|
| braze mounting | 0,30 | 0,15 | 0,08 |

